

# RM300DG-90S

HIGH POWER SWITCHING USE  
INSULATED TYPE

High Voltage Diode Module

## RM300DG-90S



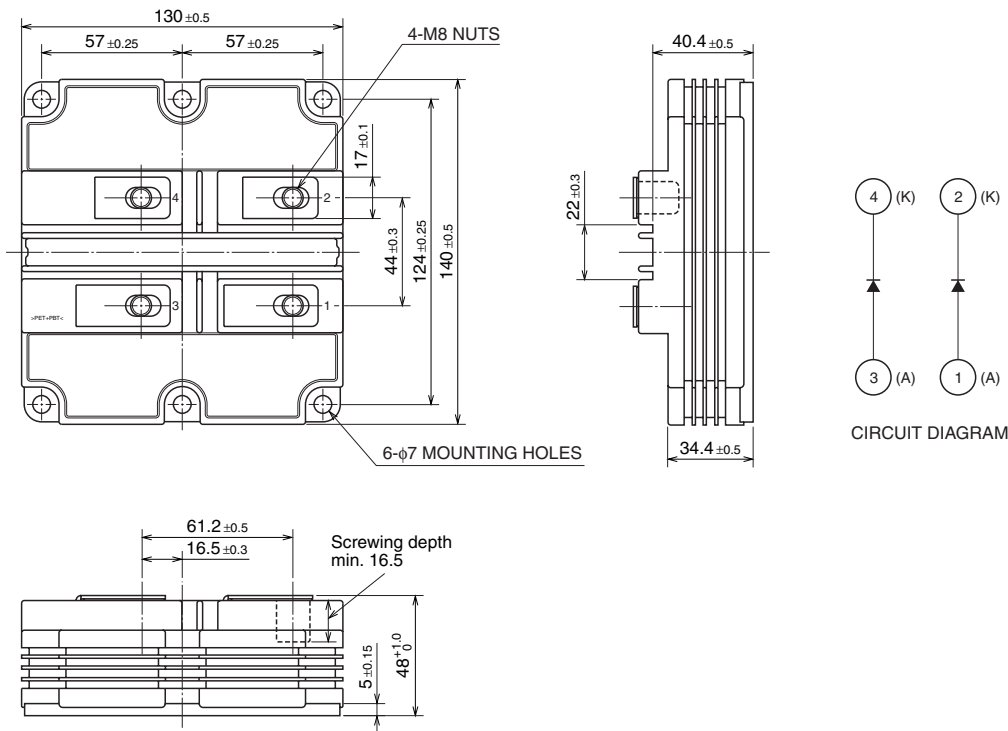
- IF .....300A
- VRRM ..... 4500V
- High Insulated Type
- 2-element in a Pack
- AISiC Baseplate

## APPLICATION

Traction drives, High Reliability Converters / Inverters, DC choppers

## OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm



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May 2009

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**MAXIMUM RATINGS**

| Symbol           | Item                                 | Conditions                                                              | Ratings    | Unit              |
|------------------|--------------------------------------|-------------------------------------------------------------------------|------------|-------------------|
| VRRM             | Repetitive peak reverse voltage      | T <sub>j</sub> = 25 °C                                                  | 4500       | V                 |
| VRSM             | Non-repetitive peak reverse voltage  | T <sub>j</sub> = 25 °C                                                  | 4500       | V                 |
| VR(DC)           | Reverse DC voltage                   | T <sub>j</sub> = 25 °C                                                  | 3000       | V                 |
| I <sub>F</sub>   | DC forward current                   | T <sub>C</sub> = 25 °C                                                  | 300        | A                 |
| I <sub>FSM</sub> | Surge forward current                | T <sub>j</sub> = 25 °C start, t <sub>w</sub> = 8.3 ms<br>Half sign wave | 2400       | A                 |
| i <sup>2</sup> t | Current-squared, time integration    | T <sub>j</sub> = 25 °C start, t <sub>w</sub> = 8.3 ms<br>Half sign wave | 24         | kA <sup>2</sup> s |
| V <sub>iso</sub> | Isolation voltage                    | Charged part to the baseplate<br>RMS sinusoidal, 60Hz 1min.             | 10200      | V                 |
| V <sub>e</sub>   | Partial discharge extinction voltage | RMS sinusoidal, 60Hz, QPD ≤ 10PC                                        | 5100       | V                 |
| T <sub>j</sub>   | Junction temperature                 | —                                                                       | -40 ~ +150 | °C                |
| T <sub>op</sub>  | Operating temperature                | —                                                                       | -40 ~ +125 | °C                |
| T <sub>stg</sub> | Storage temperature                  | —                                                                       | -40 ~ +125 | °C                |

**ELECTRICAL CHARACTERISTICS**

| Symbol           | Item                             | Conditions                                                                                                             | Limits                  |      |      | Unit |    |
|------------------|----------------------------------|------------------------------------------------------------------------------------------------------------------------|-------------------------|------|------|------|----|
|                  |                                  |                                                                                                                        | Min                     | Typ  | Max  |      |    |
| I <sub>RRM</sub> | Repetitive reverse current       | V <sub>RM</sub> = V <sub>RRM</sub>                                                                                     | T <sub>j</sub> = 25 °C  | —    | —    | 1    | mA |
|                  |                                  |                                                                                                                        | T <sub>j</sub> = 125 °C | —    | 0.5  | 10   |    |
| V <sub>FM</sub>  | Forward voltage (Note 1)         | I <sub>F</sub> = 300 A                                                                                                 | T <sub>j</sub> = 25 °C  | —    | 4.80 | —    | V  |
|                  |                                  |                                                                                                                        | T <sub>j</sub> = 125 °C | —    | 4.15 | —    |    |
| t <sub>rr</sub>  | Reverse recovery time            | V <sub>R</sub> = 2250 V, I <sub>F</sub> = 300 A<br>di/dt = -800 A/μs<br>L <sub>s</sub> =100nH, T <sub>j</sub> = 125 °C | —                       | 1.0  | —    | μs   |    |
| I <sub>rr</sub>  | Reverse recovery current         |                                                                                                                        | —                       | 280  | —    | A    |    |
| Q <sub>rr</sub>  | Reverse recovery charge          |                                                                                                                        | —                       | 250  | —    | μC   |    |
| E <sub>rec</sub> | Reverse recovery energy (Note 2) |                                                                                                                        | —                       | 0.33 | —    | J/P  |    |

Note 1. It doesn't include the voltage drop by internal lead resistance.

2. E<sub>rec</sub> is the integral of 0.1V<sub>R</sub> x 0.1I<sub>rr</sub> x dt.

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**THERMAL CHARACTERISTICS**

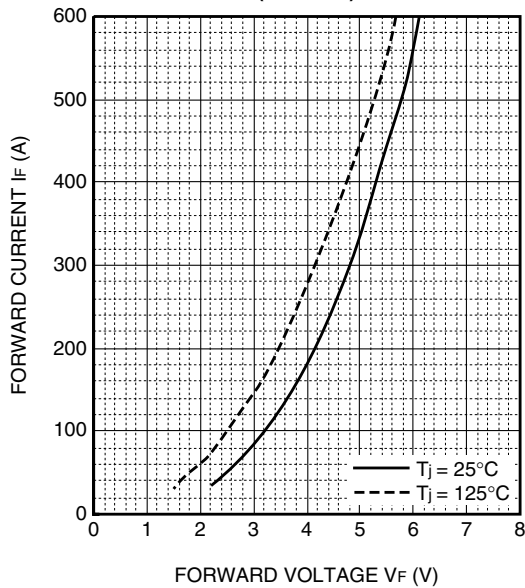
| Symbol               | Item                       | Conditions                                                                               | Limits |      |      | Unit |
|----------------------|----------------------------|------------------------------------------------------------------------------------------|--------|------|------|------|
|                      |                            |                                                                                          | Min    | Typ  | Max  |      |
| R <sub>th(j-c)</sub> | Thermal resistance         | Junction to case<br>(per 1/2 module)                                                     | —      | —    | 66.0 | K/kW |
| R <sub>th(c-f)</sub> | Contact thermal resistance | Case to Fin, λ <sub>grease</sub> = 1W/m·K<br>D <sub>(c-f)</sub> =100μm, (per 1/2 module) | —      | 48.0 | —    | K/kW |

**MECHANICAL CHARACTERISTICS**

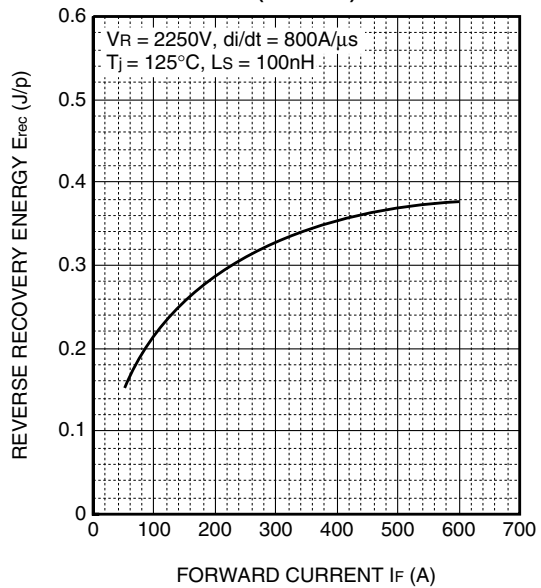
| Symbol         | Item                       | Conditions               | Limits |      |      | Unit |
|----------------|----------------------------|--------------------------|--------|------|------|------|
|                |                            |                          | Min    | Typ  | Max  |      |
| M <sub>t</sub> | Mounting torque            | M8: Main terminals screw | 7.0    | —    | 15.0 | N·m  |
| M <sub>s</sub> |                            | M6: Mounting screw       | 3.0    | —    | 6.0  | N·m  |
| m              | Mass                       | —                        | —      | 1.0  | —    | kg   |
| CTI            | Comparative tracking index | —                        | 600    | —    | —    | —    |
| D <sub>a</sub> | Clearance                  | —                        | 26     | —    | —    | mm   |
| D <sub>s</sub> | Creepage distance          | —                        | 56     | —    | —    | mm   |
| LP CE          | Internal inductance        | —                        | —      | 44   | —    | nH   |
| RCC'+EE'       | Internal lead resistance   | T <sub>c</sub> = 25 °C   | —      | 0.27 | —    | mΩ   |

**PERFORMANCE CURVES**

**FORWARD CHARACTERISTICS  
(TYPICAL)**



**REVERSE RECOVERY ENERGY  
CHARACTERISTICS  
(TYPICAL)**



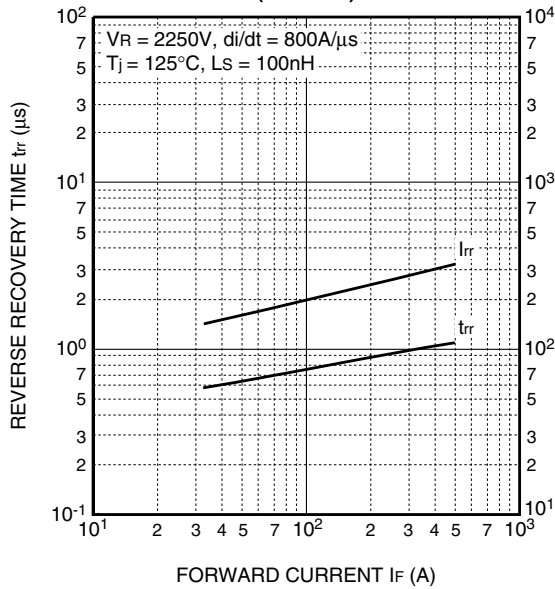
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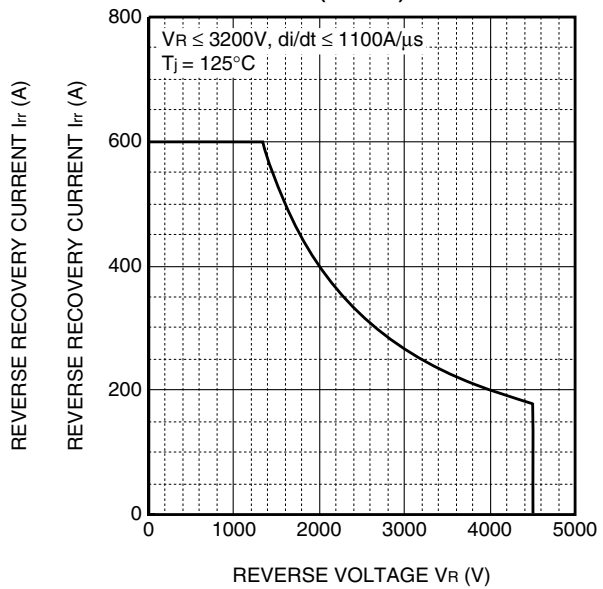
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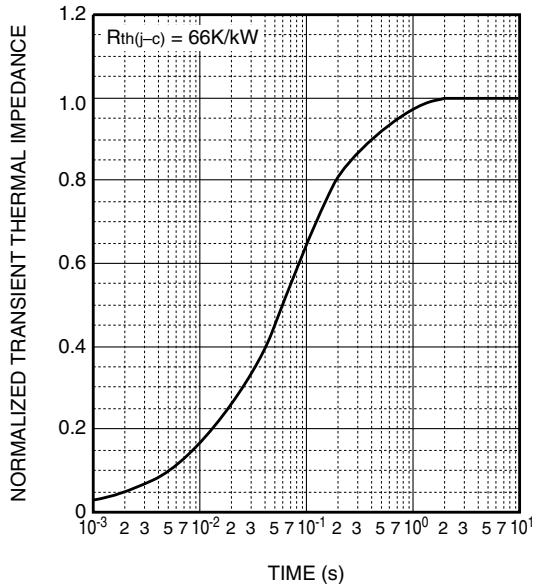
REVERSE RECOVERY CHARACTERISTICS (TYPICAL)



REVERSE RECOVERY SAFE OPERATING AREA (RRSOA)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS



$$Z_{th(j-c)}(t) = \sum_{i=1}^n R_i \left\{ 1 - \exp\left(-\frac{t}{\tau_i}\right) \right\}$$

|                       | 1      | 2      | 3      | 4      |
|-----------------------|--------|--------|--------|--------|
| R <sub>i</sub> [K/kW] | 0.0059 | 0.0978 | 0.6571 | 0.2392 |
| τ <sub>i</sub> [sec]  | 0.0002 | 0.0074 | 0.0732 | 0.4488 |

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